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INVESTIGATION OF GROUP IV-A METAL VAPOR GENERATION AND FLUX BEHAVIOR

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General Electric Company Valley Forge Space Center Philadelphia, PA 19101

May 1978



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Final Report

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AIR FORCE WEAPONS LABORATORY Air Force Systems Command Kirtland Air Force Base, NM 87117 AFWL-TR-77-240

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The vapor compositions of Sn, Ge, and Si we mass spectrometry up to temperatures where	ere investigated by high temperatur the respective vapor pressures (over
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20. ABSTRACT (Cont'd)

reached 1 torr or higher.

In the case of Sn and Si, 95 percent and 90 percent respectively, of the vapors exist in the atomic form; the rest exists in the form of dimers, trimers, and tetramers. The germanium vapor consists of 98 percent atomic species and traces of Ge_2 .

The reaction between titanium and boron was utilized to generate high density tin vapor.

Emission spectra of the Sn/N_2O system (where Sn was generated by RF heating and/or via the Ti/B reaction) suggest that the intensity of the green system SnO ($a^3\Sigma$) is reduced with increasing density of tin vapor.

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I. INTRODUCTION

The gas phase reactions of certain Group IV-A metals with N₂[']O can give rise to electronically excited metal oxide species which have been considered candidates as active molecules for electronic transition chemical lasers. The objectives of this program were to obtain experimental data on selected Group IV-A metals as they pertain to the properties of the gas phase generation and transfer and also to devise practical schemes for developing a metal vapor generator which may permit an evaluation of their potential as laser pumping sources.

IT. APPROACH

Metal atoms of Sn, Ge, and Si were generated at densities as high as 10^{17} with induction RF heating. The metal vapor flux is characterized in terms of polymer and particulate formation (in the absence and presence of foreign gases) using mass spectrometry and other techniques. The addition of N₂, N₂O, Ar, and He were investigated.

In addition, intermetallic reaction schemes were evaluated for their potential of producing the required metal flows, and a metal vapor generator was developed and tested.

III. EXPERIMENTAL

1. STUDY OF METAL VAPOR GENERATED BY RF-INDUCED HEATING

RF heating and Knudsen effusion have been used extensively in high-temperature mass spectrometric work to generate and diagnose metal vapors and their oxidation products at temperatures as high as 3000 K(1,2,3).

The experimental arrangement is shown in Figures 1 and 2. Figure 1 shows the inductively heated Knudsen cell in-place in the Bendix Model 12 time-of-flight mass spectrometer. The water-cooled induction coil enters the furnace chamber from the bottom flange. The crucible and its holder are supported on three tantalum rods on the inlet assembly.

The Knudsen crucible dimensions are 0.6 cm I.D. by 1.2 cm deep with a 0.13 cm wall with a crucible cover, 0.32 cm thick by 0.9 cm (directer), which has a 60° conical orifice whose minor diameter is 0.08 cm.

The temperature of the crucible is measured with a Leeds and Northrup optical pyrometer by sighting into the orifice (as shown in Figure 1). Corrections due to prism and window were made in all the reported temperature values.

The vapor generated in the crucible in chamber II, after traveling 2 cm through a vacuum of $P_{II} = 10^{-6}$ torr, enters chamber I (through a slit 0.5 cm by 0.05 cm) which is differentially pumped to a pressure $P_1 = 10^{-7}$ torr. The vapor travels 6 cm in chamber I before it reaches point G where an electron beam of controlled energy is

A - INDUCTION COIL

- B . TANTALUM HEAT SHIELD
- C KNUDSEN CRUCIBLE AND LID
- D WATER COOLED PORTION OF CHAMBER
- Σ MOVABLE SHUTTER
- F TOF SOURCE ENTRANCE SLIT
- **G IONIZING ELECTRON BEAM**
- H ION GRID
- I VIEWING WINDOW ON MULTIWINDOW ASSEMBLY
- J PRISM
- K OPTICAL TYROMETER



Figure 1. Knudsen Crucibia Mass Spectrometer Apparatus



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Figure 2. Inductively Heated Furnace in Time-cf-Flight Mass Spectrometer

directed perpendicular to the metal vapor beam. The interaction with the pulsed electron beam produces positive ions which are in turn pulsed by ion grid H (-2.8 kV), and all receive an equal energy impulse. Since their respective velocities vary according to their mass to charge ratios (m/e) the ions are separated in bunches of equal m/e. As each bunch strikes the collector cathode, it is converted into an electron signal, and through secondary electron emission in the electron multiplier is suplified. The resultant (suplified) electron pulses pass across a resistor, and the resulting voltage pulses (after further amplification in the wide band amplifier) are displayed on an oscilloscope screen and compose the mass spectrum. (The lighter masses appear on the left of the screen.) The oscilloscope is triggered by a pulse whose timing can be varied relative to that of the ion focus pulse. Mass spectrometer positive ion signals can also be obtained by using the analog output. The analog unit integrates many singlesweep spectra which are detected by a gate. A single-sweep spectrum results from one cycle of operation at a rate of 10⁴ per second. The gate sweeps the spectrum (at a slowly and linearly increasing time delay with respect to the ionization pulse) and represents the average of a number of ionization pulses at each mass peak. The data reported in this document were obtained by using the analog unit.

Modifications of the apparatus, which allow the study of gas phase oxidation reactions of the metal atoms, involve increasing the distance between the crucible and the entrance slit to the ion source and the introduction of the oxidant gas in the path of the metal atoms as discussed in section (d).

a. THE COMPOSITION OF TIN AND TIN OXIDE VAPORS

Data were obtained on the composition of tin vapor in the temperature range 1500 K to 2073 K. The data were analyzed in order to obtain information on the relative significance of all the species ex^{i} ting in the vapor under high concentration conditions. Typical apectra of Sn, Sn₂, and Sn₃ are shown in Figure 3. It is apparent that all seven isotopes of the tin monomer (Sn) are resolved and in terms of mass ion intensity metch very well the expected isotopic abundance, i.e.,

 $\operatorname{Sn}^{116} = 14.3\%$, $\operatorname{Sn}^{117} = 7.6\%$, $\operatorname{Sn}^{118} = 24\%$, $\operatorname{Sn}^{119} = 8.6\%$, $\operatorname{Sn}^{120} = 32.85\%$, $\operatorname{Sn}^{122} = 4.9\%$, and $\operatorname{Sn}^{124} = 5.9\%$.

In addition, the dimer, trimer, and tetramer were also observed. However, due to the many combinations of isotopes, the number of peaks increases in the formation of polymeric species; and it is for this reason that resolution of the individual peaks is difficult.

Adjustments for this effect were made by measuring the highest mass peak and multiplying it by a corresponding correction factor to account for all the isotope combinations.

The partial vapor pressures of Sn_2 , Sn_3 , and Sn_4 were computed relative to the monomer from the relationship:

 $P Sn_x = P Sn x (I Sn_x/I Sn) x (\mathcal{O}_1/\mathcal{O}_x) x C_i$



where

- P = Vapor Pressure
- = Ion Intensity
- O = Ionization Cross Section (Relative)
- C_i = Correction Factor for Isotopes

Mass spectrometry data on relative ion intensities as well as calculated ratios of vapor pressures are shown in Table 1. The computed partial vapor pressures of Sn_{χ} (x = 2, 3, 4) are shown in Figure 4. It is apparent from these data that even at the highest temperature of the measurements the contribution of the polymeric species is minor. At 2000 K where the total tin pressure is about 2 torr, only 5% of the total weight is in a form other than atomic. The relative contributions of Sn_2 , Sn_3 , and Sn_4 are 3%, 2%, and 0.2% respectively, as shown in Table 2.

In order to predict the condensation characteristics of tin oxide(s), tin oxide vapor species in equilibrium with the condensed phase of n/snO_2 mixtures were investigated mass spectrometrically in the temperature range of 1223 K to 1323 K. The resulting vapor consists of SnO, Sn_2O_2 , and Sn_3O_3 species in quantities shown in Figure 4. The total vapor pressure of the oxides in this temperature range in comparison to tin vapor is two orders of magnitude higher.

TABLE 1

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. Laiste THE COMPOSITION OF TIN VAPOR

P Sn4	10-3.3	10-3.36	10-3.06	10-2.993
I Sn I Sn4	6,709	7,611	3,805	3,250
I Sn4	9	ą	2.0	1.6
P Sn	16-3.2	10 ^{-2.25}	10-2.14	10-2.44
I Sn I Sn 3	2116	240.3	206.2	371.4
I Sn ₃	19	285	36	14
P Sn ₂	10-2.13	10 ^{-1.89}	10-1.6	10 ⁻²
I Sn I Sn ₂	135.4	77.6	39.8	108.3
I Sn ₂	297	883	191	48
I Sn	40,200	68,500	7,610	5,200
T (K)	0.56	0.48	0.495	0.58
T (K)	1783	2073	2003	1723

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TABLE 2

COMPOSITION OF TIN VAPOR AT 2000 K

 $\frac{P_{TOTAL}}{P_{Sn_1}} = 2 \text{ TORR}$ $\frac{P_{Sn_2}}{P_{Sn_1}} = 1.7 \times 10^{-2}$ $\frac{P_{Sn_3}}{P_{Sn_1}} = 6.7 \times 10^{-3}$ $\frac{P_{Sn_4}}{P_{Sn_1}} = 5.5 \times 10^{-4}$

.: ~95% OF Sn ATOMS EXIST AS Sn 3% OF Sn ATOMS EXIST AS Sn₂ 2% OF Sn ATOMS EXIST AS Sn₃ 0.2% OF Sn ATOMS EXIST AS Sn₄

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b. THE COMPOSITION OF GERMANIUM VAPOR

After realizing that tantalum was not a suitable container for liquid germanium, a tungsten crucible was used for this study. The data obtained in the temperature range 1700 K to 1865 K on the germanium system are shown in Figure 5. The dimer $Ge_2(g)$ was observed at 1865 K for the first time, and it appears to correspond to less than 2% (by weight) of the total vapor. No higher polymers were observed.

c. THE COMPOSITION OF SILICON VAPOR

The vaporization of elemental silicon was also investigated by the use of induction heating and Knudsen effusion mass spectrometry. Measurements were made on the composition of the vapor in the temperature range 1660 K to 2380 K. The data in Figure 6 show the existence of the dimer, trimer, and tetramer which collectively account for approximately 10% of the total vapor.

d. METAL/OXIDIZER REACTION SYSTEM

A system (Figure 7) was assembled to examine the oxidation species of metal atoms generated by a sample contained in an RF (25 kW, 450 KHz) heated tantalum crucible. The reaction vessel is a pyrex cylinder (15 cm I.D. by 45 cm) which has two 5 cm diameter quartz windows located 22.5 cm from either end for optical measurements. A metal plate is attached at one end of the cylinder. The RF power transmission leads terminate in a copper coil (1/4 in. tubing) mounted on the plate. Metal samples are vaporized from a tantalum crucible







Figure 7. Metal Vapor Oxidation System

(9 mm I.D. by 15 mm) mounted inside the coil as shown in Figure 7. The plate also has two gas inlet tubes and a thermocouple feed through. One gas inlet is used to pass an inert carrier gas past the heated crucible and thereby transport the metal vapor along the cylinder where reaction with oxidizer gas occurs. The second gas inlet tube supplies oxidizer gas flow. This tube is movable along the cylinder in order to vary the extent of oxidation of the metal vapor passing the optical windows. In addition, the vaporization temperature, the inert gas/oxidizer pressure, and the gas velocities are adjustable parameters.

The pyrex cylinder is attached to the high pressure side of a solenoid operated gas sampling valve. The low pressure side of this valve is mounted on the mass spectrometer flight tube near the ion source chamber. This was to allow the metal/oxidizer stream to be sampled for species analysis.

Several experiments were performed using tinshot samples RF heated to 1773 K to 2073 K in a tantalum crucible. The crucible was heated in flowing argon carrier gas with and without N_20 flow through the exidizer gas inlet. The argon pressure was 10 torr and the N_20 was 2 torr. With the crucible at 1600° C and with both Ar and N_20 flowing, a blue disc shaped flame (~1 cm diameter by 1 cm high) was observed above the crucible. The mass spectrum of the products above this flame was recorded using the high pressure gas sampling valve. The spectrum showed argon and N_20 mass peaks, but no tin or tin oxides were observed. Spectra obtained without the N_20 oxidizer also showed no Sn mass peak.

Since there was no Sn mass signel without oxidizer in the gas flowing past the crucible, work was directed toward increasing the Sn metal concentration at the sampling value pinhole. This was done by increasing the carrier gas velocity and by operating the crucible in the 2273 K to 2473 K range where the vapor pressure of tin is about 10 times higher than the previous range. Tin was vaporized in this temperature range in flowing argon at pressures from 0.3 to 20 torr. There was no tin or tin oxide mass signal when these metal vapor/gas systems were sampled with the pinhole-slide sampling value. The argon and N₂O mass peaks were readily detected. This work was done with the crucible located 27 cm from the mass spectrometer antrance slit.

In a further attempt to record tin and tin oxide mass peaks, several changes were made in the system: (1) Crucible-slit distance was reduced to 18 cm, (2) the sampling value pinhole diameter was increased from 250 to 750 micrometers, (3) the gas sampling time was increased from 0.1 to 0.5 second. A series of vaporization experiments at temperatures up to 2273 K again showed no tin or tin oxide mass signals, yet substantial amounts of tin were vaporized from the crucible in the process. It was thus concluded that serious condensation phenomena were taking place which prevented the transfer of atomic and molecular species into the ion source of the mass spectrometer, and therefore no further work was done with this system.

2. USE OF INTERMETALLIC REACTIONS FOR TIN VAPOR GENERATION

The aveilability of high density metal vapor has been considered a requirement in the development of chemically pumped laser candidate systems. Thus, a portion of this study was directed towards the study of intermetallic reactions as a means of producing high density tin. Specifically, the highly exothermic reaction leading to the formation of titanium diboride has been considered:

Ti (s) + 2B (s) \longrightarrow Ti B₂(s) + \triangle H

The exothermicity (Δ H) of this reaction is about 1.2 kcal/gm and can raise the temperature of the product TiB₂ to temperatures far in excess of the boiling points of the group IV-A elements (with the exception of carbon).

The thermochemical evaluation of the Ti/B/Sn system is shown in Table 3 where the heat released in the formation of TiB_2 can be compared to the enthalpy change of the mixture during the heating cycle and the subsequent vaporization of tin.

In providing theoretical estimates for generating tin vapor, it was assumed that the mixture is first heated to the boiling point of tin (2960 K) and at that point the excess energy is consumed in vaporising tin:

Heat of Formation of TiB₂ = Total Enthalpy Change + Heat Consumed in Sn Vaporization

or

 ΔH_{f} (TiB₂) = $(H^{o}_{2960} - H^{o}_{298})$ TiB₂

+ n $\left(H^{\circ}_{2960} - H^{\circ}_{298}\right)$ sn + n $\left(\Delta H^{\circ}_{vap}\right)$ sn where n = number of moles of Sn vaporized or 77 = 54.5 + n(20 + 69.4); therefore, n = 0.25.

TABLE 3

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PROPERTIES
HERMOCHEMICAL

	Mel	ting	Enthalpy Change	Heat of Formation	Vapori	zation
Material	M.P. (K)	∆H (kcal/mole)	^H 2960 ⁻ H ₂ 98 (kcal/mole)	$\Delta H_{\epsilon,298}$ (kcal/mole)	B.P. (K)	∆ ^H (B.P.) (kcal/mole)
Sn	505	1.7	20		2960	4.69
T1	1940	4.0	15		3575	102
8	2300	5.1	17		4200	129.2-137.9
TiB2	3193	12 ± 3	54.5	- 77	> 4000	

B.P. = BOILING POINT

M.P. = MELTING POINT

It would appear then that the formation of 1 mole of TiB₂ can theoretically generate 0.25 mole of Sn. This suggests that the desired stoichiometry should be:

Ti + 2B + 0.25 (or less) Sn

 \rightarrow TiB₂ (c) + 0.25 Sn (g)

which represents 30% Sn (or less) in terms of total mixture weight.

a. YIELD MEASUREMENTS - OPEN TUBE CONFIGURATION

Several runs were carried with Ti, B mixtures at molar ratios of 1 to 2, respectively. Tin was added at 5, 10, 15, and 20% of the total weight. The mixture was placed in a 3 cm I.D. cylindrical crucible made out of ZrC_2 and fired with a tungsten (hot) wire. The first few runs were carried out inside a quartz tube in flowing argon at 1 atmosphere. In every case, the initiation was successful and resulted in tin vapor deposits on the inner walls of the quartz tube.

The amount of tin vaporized was obtained by chemical analysis of the residue after the firing: The total residue was taken and ground to a powder; it was then thoroughly mixed, and a representative sample was taken from the total. The sample was then digested with 30% HNO₃ until all reaction had ceased. Subsequent addition of concentrated HC1 assures that all tin is in solution. After 2 hours of treatment with HC1, the samples were filtered and diluted in 100 ml volumetric flasks.

The analyses of the solutions were carried by atomic emission spectroscopy using appropriate calibration standards as shown in Figure 8.



Five such runs were analyzed. The results shown in Table 4 suggest that as expected the amount of tin vapor produced depends not only on the amount of tin added but also on the geometry of the generator. Open ZrO_2 containers vaporized 40% to 60% of the available tin (Runs 3, 4, and 5), while the presence of an orifice may constrict the flow and reduce the vapor yield considerably (Run 2).

b. YIELD MEASUREMENTS - SLOTTED TUBE CONFIGURATION

The open tube reactor was modified in such a way that the vapor would be allowed to exit easily from a slotted configuration as compared to the point source. The tested design is shown in Figures 9 and 10 where the reactor consists of a slotted graphite tube. This configuration holds 3 to 4 gms of mixture and theoretically can produce up to 1 gm of Sn vapor.

In an effort to check our analytical technique, several runs were made on mixtures which were not fired or were fired in a closed tube. Under these circumstances, it was possible to account for all added tin. When the mixtures were fired in the slotted tube, however, the residual tin was always lower than the introduced quantity.

The results of this series of experiments shown in Table 5 suggest that in this configuration 30% to 50% of the available tin is removed from the residue and assumed to convert into the vapor state. In fact, after each experiment the inside surface of the vessel housing the generator is coated with shiny films of tin (not droplets). Subsequent analysis of the material coating the vessel showed that the observed deposits are elemental tin, and as much as 50% of the missing tin (from the residue) may be recovered by this technique.

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TABLE 4

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TIN ANALYSIS IN TIB2-Sn MIXTURES

2	· + ND	SAMPLE WT (gm)	% Sn-BEFORE	Z Sn-AFTER	Z Sn-REMOVED
	la	50.14	ŝ	2.06	2.94
	2 ⁸	49.95	10	7.43	2.57
	з ^р	49.50	10	4.01	5.99
-	4 ^b	49.70	15	8.28	6.72
•	5 b	49.47	20	10.09	16.9

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- Cap with 0.3 cm nozzle orifice was placed on $2r0_2$ crucible

- Cap was removed

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Figure 9. Tin Vapor Generator

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F - TUBE OPENING, 0.015 in. WIDTH, 3.25 in. LENGTH





TABLE 5

TIN ANALYSIS IN THE T1/B/Sn SYSTEM

Sn-REMOVED		0	60.7	46.7	46.9	35	24.8	57	42.3	33.5	43.4 AVE.
Z Sn REMOVED	0	0	2.89	4.25	6.1	5.85	1.18	5.19	5.5	5.6	
Z Sn AFTER	20	20	1.87	4.84	6.9	10.85	3.58	3.91	7.5	11.1	
Z Sn BEFORE	20	20	4.76	9.1	13	16.7	4.76	9.1	13	16.7	
SAMPLE WEIGHT (gm)	3.5	3.5	3.15	3.3	3.45	3.6	3.1	. 3.3	3.5	3.6	
RUN #	6 ⁸	4 ²	8c	о б	10 ^c	11 ^c	12 ^c	13 ^c	14 ^c	15 ^c	

- Not fired

æ

b - Fired in closed system

c - Fired in slotted reactor

3. EMISSION SPECTRA OF Sn-N₂O SYSTEM

Spectra were taken of the plume radiation from Sn vapor reacting with N₂O gas. The spectra were taken using a 1.5 meter (Bausch & Lomb) Grating Spectrograph equipped with a cylindrical condensing lens. The lens-spectrograph entrance slit orientation was adjusted to record the radiation from a line image located at the center of the tantalum crucible from the top edge upward to a point 5 cm above the crucible. Spectra were recorded on Kodak Tri-X film using a 60 micrometer spectrograph entrance slit. The exposure was integrated over the entire run in each series of experiments; i.e., 0.2 to 0.5 second for the Ti-B series and 2 to 3 minutes for the RF heated series. First and second order spectra were recorded covering the following wavelength range: $3600 \stackrel{\circ}{A}$ to 7200 $\stackrel{\circ}{A}$ first order and 1950 $\stackrel{\circ}{A}$ to 3600 $\stackrel{\circ}{A}$ second order. Table 6 gives a listing of the Sn and SnO species identified. Two series of experiments were run.

In the first series, a stoichiometric mitture of Ti & B powder (1.5g) was mixed with 50% Sn powder (by weight). Samples were contained in a tantalum crucible which had a slotted lid (1.5 by 14 mm slot) and fired using a hot nichrome wire. Experiments were run in a vacuum tank in which N₂O flowed through a small diameter metal tube located 2 cm above the crucible. Runs were made at 10 and 20 torr N₂O; the plumes were 10 to 12 cm wide, extended from 1 to 2 cm below the N₂O inlet to 10 to 12 cm above, and produced intense flashes of yellow, green and blue. The spectrum of the lower 5 cm at the center of these plumes showed 6 bands of the SnO blue system $(D \longrightarrow X)$.

TABLE 6

EMISSION SPECTRA OF THE Sn-N2O SYSTEM

A. SnO

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System	Band Heads o Wavelength (A)	<u>v'</u>	<u>v"</u>	Exp Co	erime nditi	ntal ons
• • • • • •						
D¹ℋ⋧⋧x⁺∑Ţ	3691.4	0	3	*	+	0
(A) -	3802.7	0	4	*	+	0
Reference 4	3721.2	1	4	*	+	0
	3752.3	2	5	*	+	с)
	3899.3	3	7	*	+	0
	3864.8	2	6	*	+	0
	3703.2	3	0		+	0
	3779.9	2	Ō		+	0
	3863.5	1	Ō		+	0
	3948.5	ō	Ū		+	0
1 +	3978.8	4	3		+	0
cz≥x⁺∑Ť	4026.9	2	2		+	Ó
	4079.9	ō	1		+	Ó
Reference 5	4121.9	i	2		+	Ō
	4218.8	ō	2			Ó
	4262.3	· 1	3			Ō
	4302.2	2	4			Ō
	4411.6	ī	Å			Ō
	4452.5	2	5			ŏ
	4499.1	3	6			0
. . .	5788.4	0	2			0
$_{3}\Gamma^{+} x^{1}\Gamma^{+}$	5535.4	õ	1			ō
	5371.5	5	3			ō
Reference 6	5300.0	-	-			-
	6064.5	0	3			0

See footnotes at end of table for definition of experimental conditions.

TABLE 6 (Cont'd)

B. Sn Lines (Reference 7)

Wavelength (Å)	Term Lower Upper	Experi Condi	imental Itions
2863.3	$5P^2 {}^3P_0 - 6S {}^3P_1^0$	+	0
2840.0	$5P^2 {}^3P_2 - 6S {}^3P_2^0$	+	0
3801.0	$5P^{2}D_{2} - 6P^{3}P_{1}^{\sigma}$	+	0
4524.7	$5P^{2} S_{0}^{1} - 6S P_{1}^{1}$	+	0

* = Ti-B seeded with 50% Sn

+ = RF heated Sn (slotted lid)

0 = RF heated Sn (no lid)

In the second series of experiments, high purity tin shot was vaporized using a 25 kW, 450 KHz induction heater coupled by way of a copper coil to the tantalum crucible. Runs were made with a crucible covered with a slotted lid (1.5 mm by 14 mm) as well as with an open crucible. N₂O pressure was varied from 0.5 torr to 10 torr and the temperature ranged from 1373 K to 2373 K. The slotted lid runs produced a blue disc-shaped plume 2 to 3 mm above the crucible. The disc was 3 to 4 cm in diameter and 1 to 1.5 cm thick. It was brightest at 2 mm N₂O pressure and 1873 K to 2073 K crucible temperature. Spectra taken at 2 to 3 minutes exposure time showed the SnO blue $D \longrightarrow K$ and C-->X systems. The most sensitive Sn lines (2840 $\stackrel{\circ}{A}$ and 2863 $\stackrel{\circ}{A}$) were weak on the film probably due to self absorption in the high density Sn vapor. However, two upper state Sn lines (3801 Å and 4525 Å) appeared at an intensity level judged to be 50 to 100 times that of the sensitive Sn lines. This suggests that the Sn-N₂O system is producing a nonthermal energy distribution of Sn.

Several runs were made with an open tantalum crucible. A pale green fringe was seen at the top of the blue disc plume at 1573 K to 1673 K and 2 torr N₂O. With increasing temperature and/or N₂O pressure, the green disappeared. Spectra taken during these runs showed strong SnO blue (D \longrightarrow X and C \longrightarrow X) and weak SnO green (a \longrightarrow X) bands. The Sn 2840 Å and 2853 Å lines were weak while the 3801 Å and 4525 Å lines were medium intensity.

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IV. CONCLUSIONS

Based on results gathered in the course of this study, the following conclusions can be made:

1. Based on mass spectrometric studies, the composition of tin vapor in the temperature range 1500 K to 2073 K consists mainly of tin atoms (Sn). Small quantities of dimers (Sn₂), trimers (Sn₃) and tetramers (Sn₄) contribute less than 5% to the total weight.

It is thus concluded that under the temperature/pressure conditions required for high vapor densities, the formation of polyatomic species is not expected to the up a significant number of the atoms which are considered necessary in the proposed pumping scheme which leads to electronically excited SnO*.

2. The composition of germanium vapor in the torr-regime consists essentially of monatomic Ge (98%) and a very small amount of dimer Ge₂ (2%). No higher molecular weight species were observed in the temperature range 1700 K to 2000 K.

3. The composition of silicon vapor is somewhat more complex. In the vicinity of 2500 K where the vapor pressure exceeds 1 torr, the vapor in addition to Si atoms contains Si₂, Si₃, and Si₄, comprising about 10% of the total.

4. The volatility of tin oxide is higher than that of the tin metal by two orders of magnitude; this is a desirable property in terms of attempting to build a laser on the tin oxide system.

5. The high exothermicity of the Ti/B reaction has been utilized to vaporize tin in relatively large quantities. Several grams of tin can be vaporized over a period of 1 second by this technique. Favorable conditions for effective vaporization have been identified, and a small tube-like generator was built.

6. The limited study of the emission spectra of the Sn-N₂O system suggests that the SnO green system ($a^3 \sum + - x^1 \sum + x^1 \sum + x^1$) appears only at low Sn densities as dictated by low temperatures (1473 K to 1673 K). In the 1673 K to 2270 K range the green system is replaced by the blue $C \longrightarrow X^1 \sum + x^1$

Appearance of the upper state Sn lines at 3801 Å and 4524 Å at high intensity suggests a nonthermal Sn distribution.

7. Based on qualitative observations of the Sn/N_2O system, it can be stated that Sn vapor (in contrast with other metals) burns with difficulty in ambient N_2O , and the intensity of green system appears to decrease when the density of the tin vapor increases.

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